



## F. Silicon and Group-IV Devices and Integration Technology 분과

2021년 1월 29일(금), 10:45-12:15 / 채널 B

### [FB2-F] New Device Technology

좌장: 구민석 교수 (인천대학교), 김장현 교수 (부경대학교)

<b>FB2-F-1</b> <b>10:45-11:00</b>	<b>Physical Modeling of Plasma-Wave Transistors for Both Resonant and Non-Resonant THz Detection Mechanism</b> Jong Yul Park, Min Woo Ryu, Sung-Ho Kim, Yoo Bin Song, and Kyung Rok Kim <i>Department of Electrical Engineering, UNIST</i>
<b>FB2-F-2</b> <b>11:00-11:15</b>	<b>Single Transistor Latch Using Fully-depleted Silicon-On-Insulator Device</b> Gisu Youm and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>
<b>FB2-F-3</b> <b>11:15-11:30</b>	<b>Impact of Using HfO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> Multilayer on the Performance of Threshold Switching Device</b> Sojin Jeong and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>
<b>FB2-F-4</b> <b>11:30-11:45</b>	<b>Content-Addressable Memory (CAM) based on Nanoelectromechanical (NEM) Memory Switches for Low-Energy and High-Speed Operation</b> Jae Seong Lee and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i>
<b>FB2-F-5</b> <b>11:45-12:00</b>	<b>Effects of Nanosecond Laser Annealing on Highly-Phosphorus Doped Silicon</b> Hyunsu Shin, Eunjung Ko, Juhee Lee, Hwa-yeon Ryu, and Dae-Hong Ko <i>Department of Material Science and Engineering, Yonsei University</i>
<b>FB2-F-6</b> <b>12:00-12:15</b>	<b>Experimental Study of Boosting Effect in Metal-Ferroelectric-Metal Capacitor</b> Gwon Kim and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>